

1. sign of effective mass depends generally on $\frac{\partial^2 E}{\partial k^2}$.

This assumption is valid at the edge of E_c & E_v however for this problem we have stretched it further!

$$A \& D : \frac{\partial^2 E}{\partial k^2} < 0 \Rightarrow m_e^* < 0$$

$$B \& C : \frac{\partial^2 E}{\partial k^2} > 0 \Rightarrow m_e^* > 0$$

2. $E = E_0 + E_1 \cos[\alpha(k - k_0)]$

$$k_0 : k @ \min E$$

$$\text{Close to min : } m_e^* = \frac{\hbar^2}{\frac{\partial^2 E}{\partial k^2}} = \frac{\hbar^2}{E_1 \alpha^2}$$

3. $g_v(E) = \frac{4\pi}{h^3} (2m_p^*)^{3/2} \sqrt{E_v - E}$ ← Density of states (valence band)

As the question is looking in the range of E_v to $E_v - kT$

We should pay attention to D.O.S of valence band!

Table B.4 : @ $T = 300 \text{ K}$ $m_{p-\text{GaAs}}^* = 0.45 m_0$

$$m_0 = 9.1 \times 10^{-31} \text{ kg}$$

$$g_T = \int_{E_v - kT}^{E_v} g_v(E) dE = \frac{4\pi (2m_p^*)^{3/2}}{h^3} \int_{E_v - kT}^{E_v} \sqrt{E_v - E} dE$$

$$\Rightarrow g_T = \frac{4\pi (2m_p^*)^{3/2}}{h^3} \left(-\frac{2}{3} \right) (E_v - E)^{3/2} \Big|_{E_v - kT}^{E_v} \quad @ T = 300 \text{ K}$$

$$= 5.65 \times 10^{-24} \frac{1}{\text{m}} = 5.65 \times 10^{-3} \text{ B}$$

$kT = 25.8 \text{ eV} \rightarrow \text{Remember to convert to Joules}$

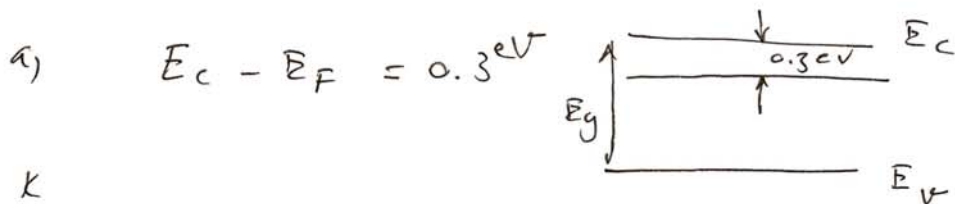
4. $f_F(E) = \frac{1}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$

a) $E - E_F = kT \Rightarrow f_F(E) = \frac{1}{1 + \exp(1)} \approx 0.269$

b) $E - E_F = 5kT \Rightarrow f_F(E) = \frac{1}{1 + \exp(5)} \approx 6.69 \times 10^{-3}$

c) $E - E_F = 10kT \Rightarrow f_F(E) = \frac{1}{1 + \exp(10)} \approx 45.4 \times 10^{-6}$

5. $E_g = 1.12 \text{ eV}$ for Si @ $T = 300 \text{ K}$



$\Rightarrow E_F - E_V = E_g - (E_c - E_F)$
 $\approx 1.12 - 0.3$
 $= 0.82 \text{ eV}$

$T = 300 \text{ K}$

$$f_F(E_c) = \frac{1}{1 + \exp\left(\frac{0.3}{25.8 \text{ mV}}\right)} \approx 8.9 \times 10^{-6}$$

\approx probability of having an electron in the lower edge of Conduction band (E_c)

$T = 300 \text{ K}$

$$f_F(E_v) = \frac{1}{1 + \exp\left(\frac{-0.82}{25.8 \text{ mV}}\right)} \approx 1$$

chance of existing a hole at the upper edge of valence band:

$$1 - f_F(E_v) = \frac{\exp\left(\frac{-0.82}{25.8 \text{ mV}}\right)}{1 + \exp\left(\frac{-0.82}{25.8 \text{ mV}}\right)} \approx 1.57 \times 10^{-14}$$

Be careful with the math as these numbers are very small! and no calculation is prone to error when comes to divisions...

5 Contd

b) $E_F - E_V = 0.4 \text{ eV} \Rightarrow E_C - E_F = E_g - 0.4 = 0.72 \text{ eV}$

$$f_F(E_C) = \frac{1}{1 + \exp\left(\frac{0.72}{25.8 \text{ mV}}\right)} \approx 7.58 \times 10^{-13} \quad \swarrow \text{probab. of electron at } E_C$$

b

$$1 - f_F(E_V) = \frac{\exp\left(-\frac{0.4}{25.8 \text{ mV}}\right)}{1 + \exp\left(-\frac{0.4}{25.8 \text{ mV}}\right)} \approx 1.84 \times 10^{-7} \quad \swarrow \text{probab. of hole at } E_V$$

6

$$f_F(E) = \frac{1}{1 + \exp\left(\frac{E - E_F = 0.55 \text{ eV}}{K_B T}\right)} = 10^{-6} \Rightarrow K_B T \approx 39.81 \text{ mV}$$

(a) $T = 300 \Rightarrow K_B T = 25.8 \text{ mV}$

$$\Rightarrow T \approx 463 \text{ K}$$